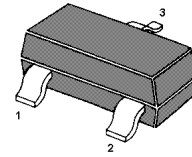
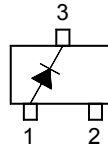


MMBD4448

Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High Conductance



Marking Code: **5D**
SOT-23 Plastic Package

Applications

- For general purpose switching

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Forward Continuous Current	I_{FM}	500	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	2 4	A
		at $t = 1\text{ s}$ at $t = 1\ \mu\text{s}$	
Power Dissipation	P_d	350	mW
Junction and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150^\circ\text{C}$	I_R	- - - -	25 2.5 30 50	nA μA μA μA
Junction Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_j	-	4	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\ \Omega$	t_{rr}	-	4	ns

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121509007
ISO 9001 : 2008 Certificate No. 50114012
OHSAS 18001 : 2007 Certificate No. 05131500006
IECQ QC 080000 Certificate No. E0241000741002

Dated : 15/06/2012

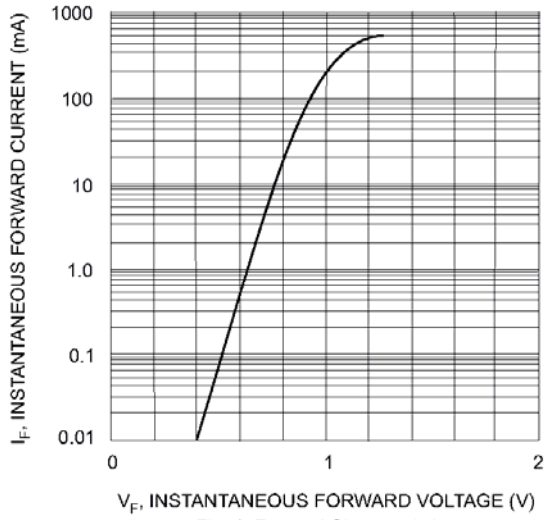


Fig. 1 Forward Characteristics

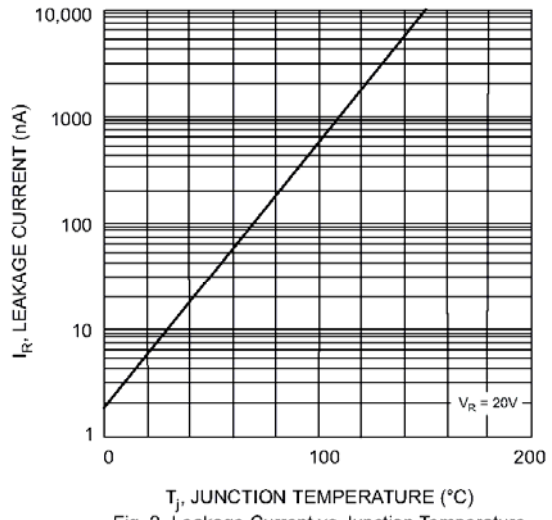


Fig. 2 Leakage Current vs Junction Temperature